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Semiconductor device manufacturing method - involves removing remnant mask layer by high frequency wet etching after polishing photo silicate glass film

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Patent Family

Patent Number	Kind	Date	Application Number	Kind	Date	Week	Type
JP 10233439	A	19980902	JP 9750919	A	19970219	199845	B

Priority Applications (Number Kind Date): JP 9750919 A (19970219)

Patent Details

Patent	Kind	Language	Page	Main IPC	Filing Notes
JP 10233439	A		8	H01L-021/76	

Abstract:

JP 10233439 A

The method involves etching a predefined area of a semiconductor substrate (2) using a mask layer (3) to form a groove (4). A PSG film (5) is then formed on the surface of the substrate by a plasma CVD process.

The PSG film is polished by a chemomechanical polish process so that the mask layer is exposed. The remaining mask layer is removed by performing high frequency wet etching.

ADVANTAGE - Reduces manufacturing time by reducing the number of processes. Element isolation characteristics are improved by polishing PSG film suitably.

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Dialog® File Number 351 Accession Number 12110370